



Docket No.: 8733.713.10-US  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Han-Wook HWANG

Confirmation No.: 9469

Application No.: 10/733,237

Group Art Unit: 2822

Filed: December 12, 2003

Examiner: Amir Zarabian

For: POLY-CRYSTALLINE THIN FILM  
TRANSISTOR AND FABRICATION  
METHOD THEREOF

Customer No.: 30827

**REQUEST FOR RECONSIDERATION**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action, mailed March 30, 2005, wherein pending claims 10-20 have rejected, Applicant respectfully request favorable reconsideration in view of the remarks presented herein below.

In paragraph 3 of the Office Action ("Action"), the Examiner rejects claims 10-20 under 35 U.S.C. §102(b) as allegedly being anticipated by U.S. Patent No. 6,788,108 to Miyake et al. ("Miyake"). Applicant respectfully traverses this rejection.

In order to support a rejection under 35 U.S.C. §102, the cited reference must disclose each and every claimed element. In the present case, claims 10-20 are not anticipated by Miyake because Miyake fails to disclose each and every claimed element as discussed below.

Independent claim 10 defines a method of fabricating a poly-crystalline thin film transistor. The method includes, *inter alia*, forming a poly-crystalline semiconductor layer on a buffer layer on a substrate; forming a gate insulation layer over the poly-crystalline semiconductor, wherein the gate insulating layer is formed with a first thickness at a channel position and at source and drain positions, and with a second thickness at offset positions, wherein the thickness of the gate insulation layer tapers in sequential doping positions from the second thickness to the first thickness.

In rejecting claim 10, the Examiner asserts that Miyake disclosing forming a gate insulation layer as claimed in as much as Miyake discloses a forming a gate insulating film 5006 over island-like semiconductor layers 5003-5005. To support this assertion the Examiner points to FIGs. 7a-c and 8a-c of Miyake. This assertion is unfounded.

Nowhere in Miyake is there any disclosure or suggestion of the gate insulating film 5006 having a first thickness in the source, drain and channel positions, and a second thickness at offset positions, much less wherein the thickness tapers in sequential doping positions from the second thickness to the first thickness. Accordingly, independent claim 10 is patentably distinguishable over Miyake.

Claims 11-20 variously depend from independent claim 10. Therefore, claims 11-20 are patentably distinguishable over Miyake for at least those reasons presented above with respect to claim 10. Accordingly, Applicant respectfully requests reconsideration and withdrawal of the rejection claims 10-20 under 35 U.S.C. §102.

The application is in condition for allowance. Notice of same is earnestly solicited. Should the Examiner have any questions regarding this application, he is invited to call the undersigned at the telephone number provided below.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. § 1.136, and any additional fees required under 37 C.F.R. § 1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

Dated: July 27, 2005

Respectfully submitted,

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